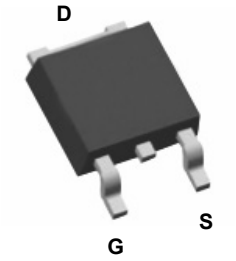
GOOD-ARK SEMICONDUCTOR

GSGD1520

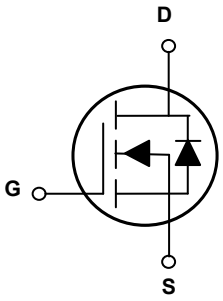
150V N-Channel MOSFET

Main Product Characteristics

V_{DS}	150V
$R_{DS(ON)}$	65mΩ
I_D	20A



TO-252 (DPAK)



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

RoHS Compliant

Description

The GSGD1520 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	20	A
Drain Current-Continuous (T_C=100°C)		14	
Drain Current-Pulsed	I_{DM}	80	A
Single Pulse Avalanche Energy[5]	E_{AS}	65	mJ
Maximum Power Dissipation	P_D	68	W
Derating Factor		0.45	W/°C
Thermal Resistance, Junction-to-Case[2]	$R_{\theta JC}$	2.2	°C/W
Operating Junction Temperature Range	T_J	-55 To +175	°C
Storage Temperature Range	T_{STG}	-55 To +175	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	150	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=150V, V_{GS}=0V	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
On Characteristics[3]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250μA	2.5	3.3	4.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A	-	59	65	mΩ
Forward Transconductance	g_{fs}	V_{DS}=5V, I_D=10A	15	-	-	S
Dynamic and Switching Characteristics[4]						
Input Capacitance	C_{lss}	V_{DS}=75V, V_{GS}=0V, F=1MHz	-	600	-	pF
Output Capacitance	C_{oss}		-	74.7	-	
Reverse Transfer Capacitance	C_{rss}		-	10.8	-	
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=75V, R_L=7.5Ω, R_G=3Ω, V_{GS}=10V	-	9.5	-	nS
Turn-On Rise Time	t_r		-	5.5	-	
Turn-Off Delay Time	$t_{d(off)}$		-	12.5	-	
Turn-Off Fall Time	t_f		-	3	-	
Total Gate Charge	Q_g	V_{DS}=75V, I_D=10A, V_{GS}=10V	-	12	-	nC
Gate-Source Charge	Q_{gs}		-	5.7	-	
Gate-Drain Charge	Q_{gd}		-	2.7	-	
Drain-Source Diode Characteristics						
Diode Forward Current[2]	I_S		-	-	20	A
Diode Forward Voltage[3]	V_{SD}	V_{GS}=0V, I_S=10A	-	-	1.2	V
Reverse Recovery Time	t_{rr}	I_F=I_S, di/dt=100A/μs[3], T_J=25°C	-	29	-	nS
Reverse Recovery Charge	Q_{rr}		-	130	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design.
5. EAS condition:TJ=25℃,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25Ω

Typical Electrical and Thermal Characteristic Curves

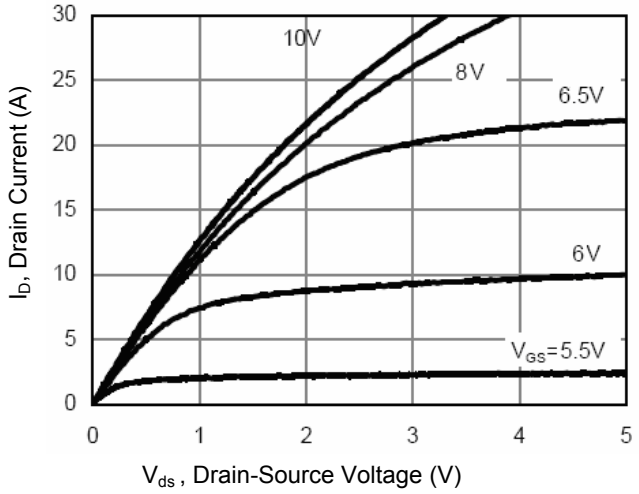


Figure 1. Output Characteristics

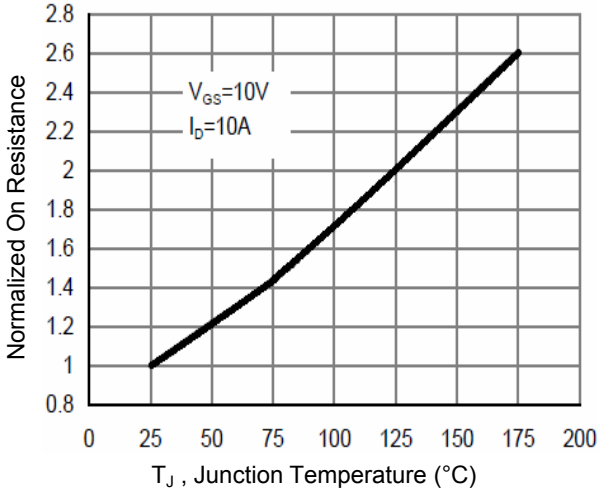


Figure 2. R_{DSON}-Junction Temperature

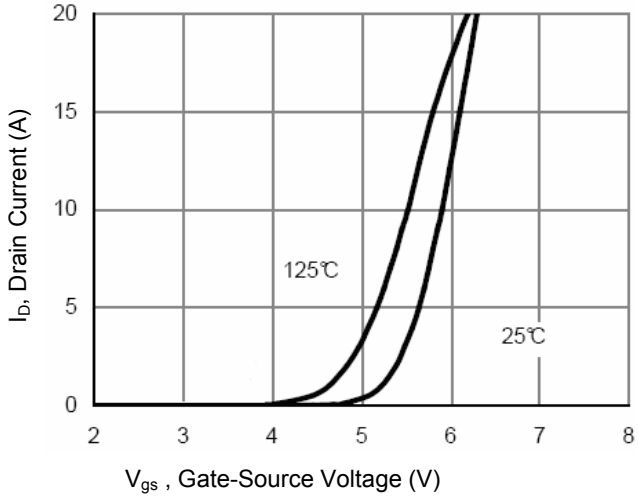


Figure 3. Transfer Characteristics

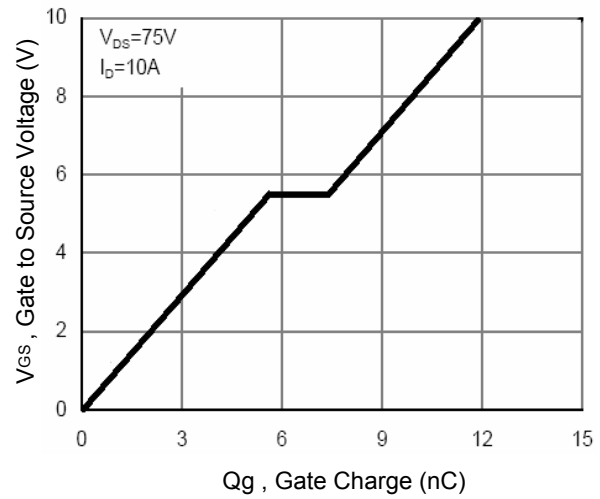


Figure 4. Gate Charge Waveform

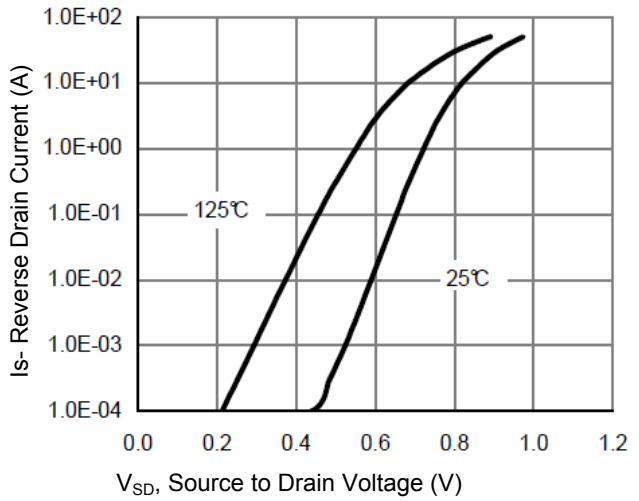


Figure 5. Source-Drain Diode Forward

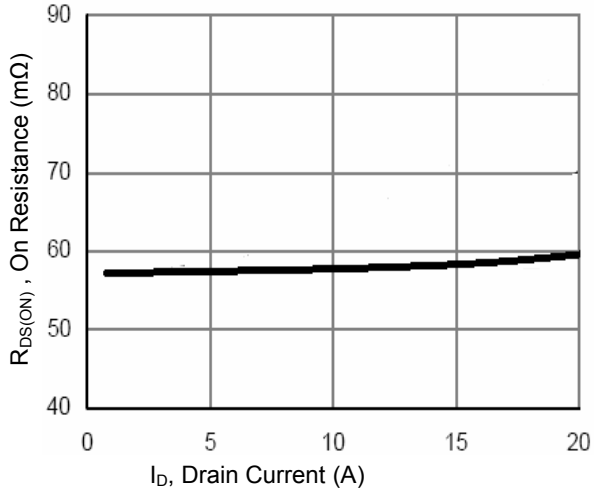


Figure 6. R_{dson}-Drain Current

Typical Electrical and Thermal Characteristic Curves

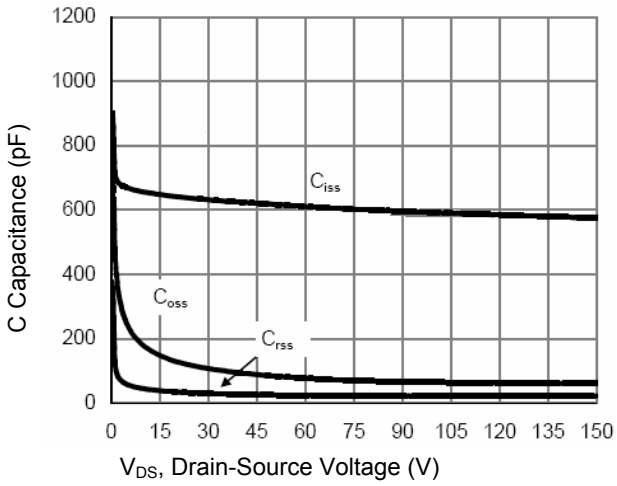


Figure 7. Capacitance vs. V_{DS}

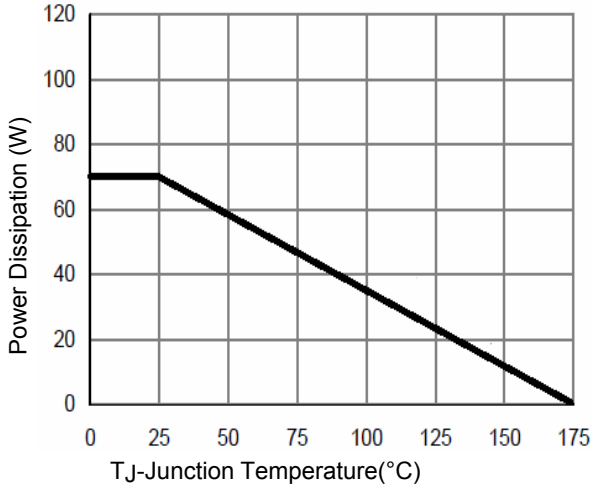


Figure 8. Power De-rating

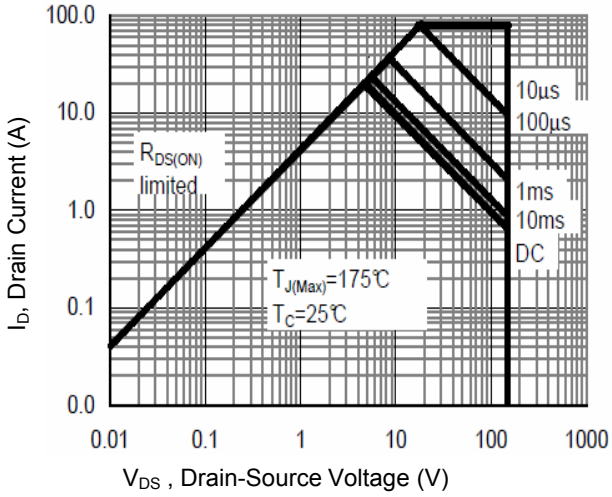


Figure 9. Safe Operation Area

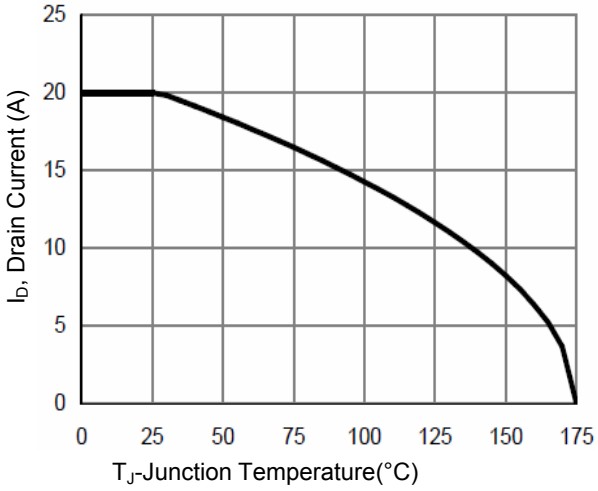


Figure 10. Current De-rating

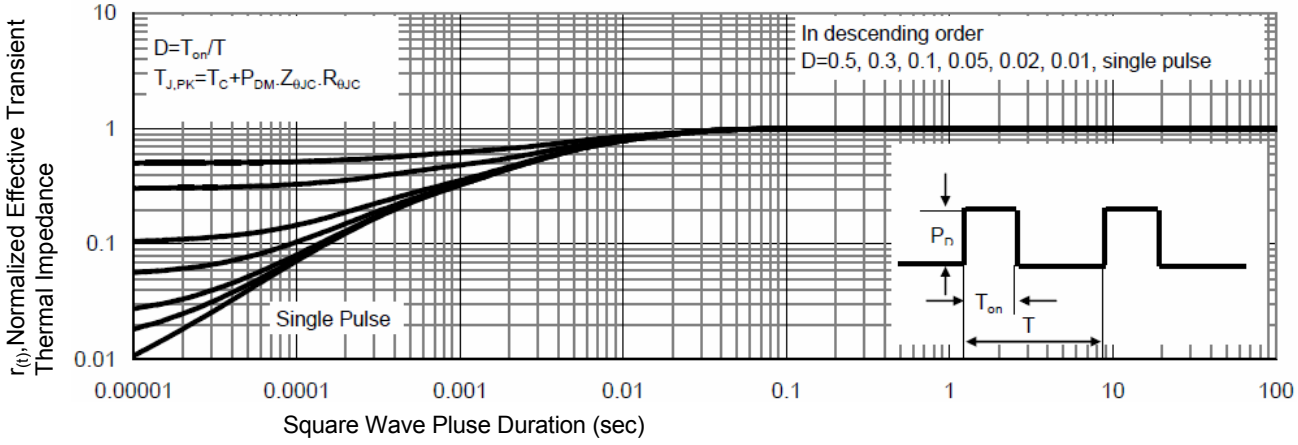


Figure 11. Normalized Maximum Transient Thermal Impedance

Typical Electrical and Thermal Characteristic Curves

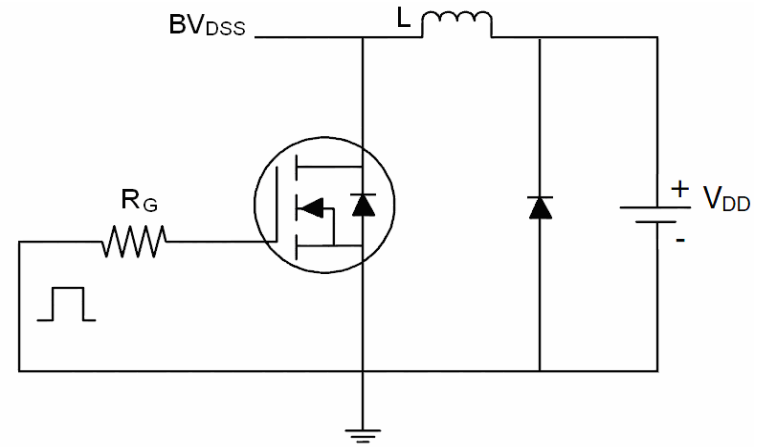


Figure 12. E_{AS} Test Circuit

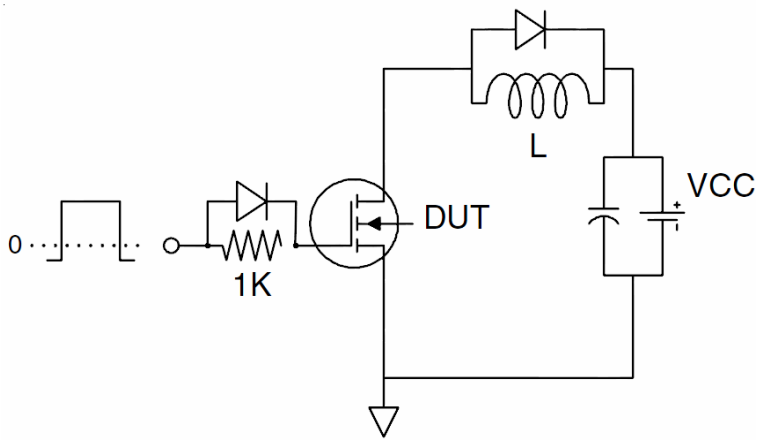


Figure 13. Gate Charge Test Circuit

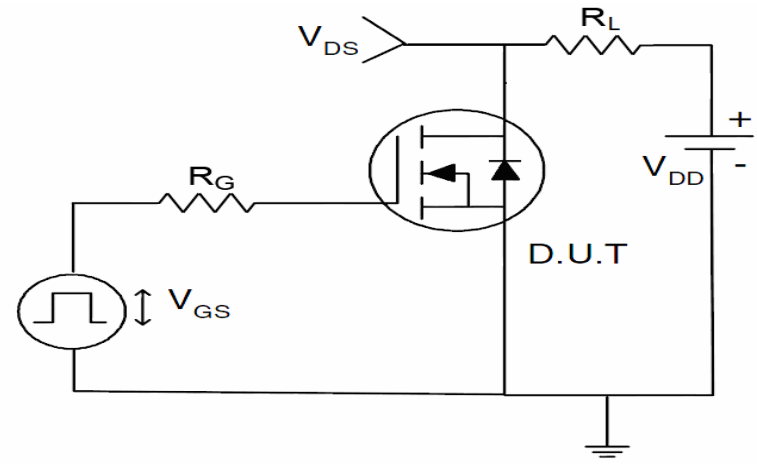
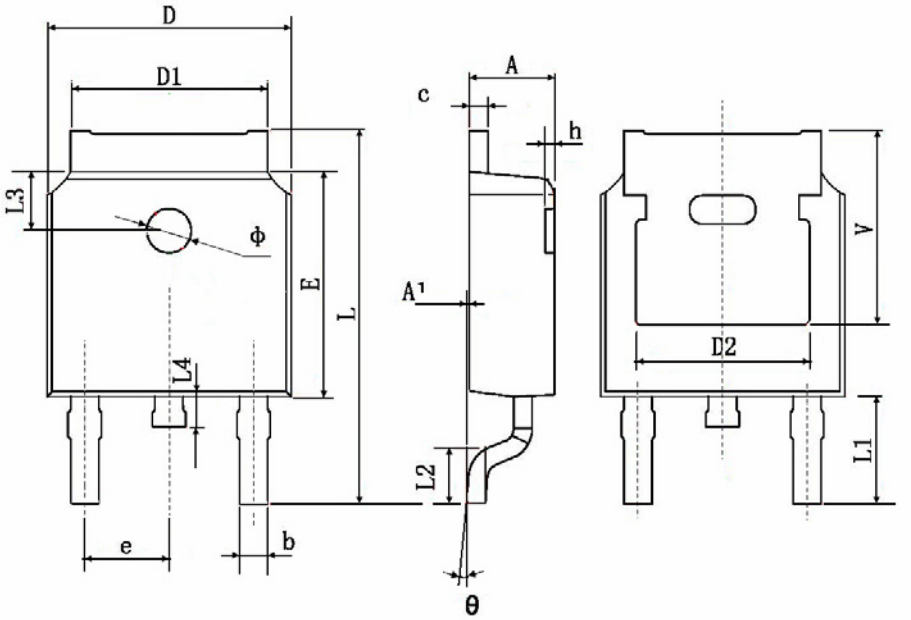


Figure 14. Switch Time Test Circuit

Package Outline Dimensions (TO-252)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	